Complementary Silicon Power Transistors

2N3055(NPN), MJ2955(PNP)

Complementary silicon power transistors are designed for general−purpose switching and amplifier applications.

Features

- DC Current Gain − h_{FE} = 20−70 @ I_C = 4 Adc
- Collector−Emitter Saturation Voltage − $V_{CE(sat)}$ = 1.1 Vdc (Max) @ I_C = 4 Adc
- Excellent Safe Operating Area
- Pb−Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	60	Vdc
Collector−Emitter Voltage	V_{CER}	70	Vdc
Collector−Base Voltage	V_{CB}	100	Vdc
Emitter−Base Voltage	V_{EB}	7	Vdc
Collector Current − Continuous	I_C	15	Adc
Base Current	I_B	7	Adc
Total Power Dissipation @ T_C = 25°C Derate Above 25°C	P_D	115 0.657	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

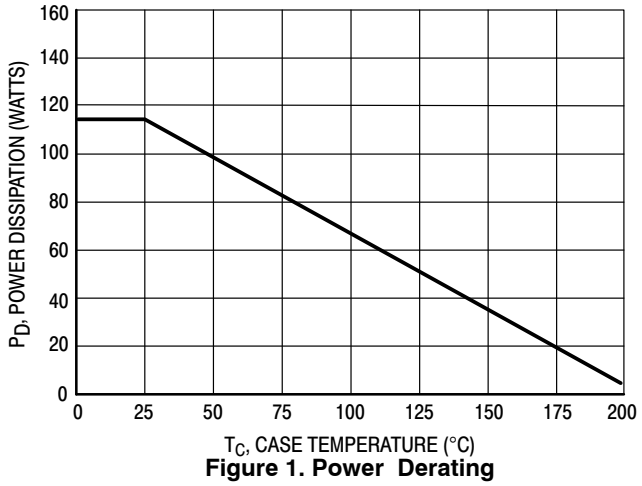
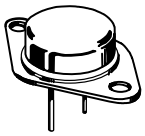


Figure 1. Power Derating

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

15 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 60 VOLTS, 115 WATTS



TO−204AA (TO−3)
CASE 1−07
STYLE 1

MARKING DIAGRAM

xxxx55	=	Device Code xxxx = 2N30 or MJ20
G	=	Pb−Free Package
A	=	Location Code
YY	=	Year
WW	=	Work Week
MEX	=	Country of Orgin

ORDERING INFORMATION

Device	Package	Shipping
2N3055	TO−204AA	100 Units / Tray
2N3055G	TO−204AA (Pb−Free)	100 Units / Tray
MJ2955	TO−204AA	100 Units / Tray
MJ2955G	TO−204AA (Pb−Free)	100 Units / Tray

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	1.52	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS*				
Collector−Emitter Sustaining Voltage (Note 1) (I_C = 200 mAdc, I_B = 0)	$V_{CEO(sus)}$	60	–	Vdc
Collector−Emitter Sustaining Voltage (Note 1) (I_C = 200 mAdc, R_{BE} = 100 Ω)	$V_{CER(sus)}$	70	–	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, I_B = 0)	I_{CEO}	–	0.7	mAdc
Collector Cutoff Current (V_{CE} = 100 Vdc, $V_{BE(off)}$ = 1.5 Vdc) (V_{CE} = 100 Vdc, $V_{BE(off)}$ = 1.5 Vdc, T_C = 150°C)	I_{CEX}	 – –	 1.0 5.0	mAdc
Emitter Cutoff Current (V_{BE} = 7.0 Vdc, I_C = 0)	I_{EBO}	–	5.0	mAdc
ON CHARACTERISTICS* (Note 1)				
DC Current Gain (I_C = 4.0 Adc, V_{CE} = 4.0 Vdc) (I_C = 10 Adc, V_{CE} = 4.0 Vdc)	h_{FE}	 20 5.0	 70 –	–
Collector−Emitter Saturation Voltage (I_C = 4.0 Adc, I_B = 400 mAdc) (I_C = 10 Adc, I_B = 3.3 Adc)	$V_{CE(sat)}$	 –	 1.1 3.0	Vdc
Base−Emitter On Voltage (I_C = 4.0 Adc, V_{CE} = 4.0 Vdc)	$V_{BE(on)}$	–	1.5	Vdc
SECOND BREAKDOWN				
Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 40 Vdc, t = 1.0 s, Nonrepetitive)	$I_{s/b}$	2.87	–	Adc
DYNAMIC CHARACTERISTICS				
Current Gain − Bandwidth Product (I_C = 0.5 Adc, V_{CE} = 10 Vdc, f = 1.0 MHz)	f_T	2.5	–	MHz
*Small−Signal Current Gain (I_C = 1.0 Adc, V_{CE} = 4.0 Vdc, f = 1.0 kHz)	h_{fe}	15	120	–
*Small−Signal Current Gain Cutoff Frequency (V_{CE} = 4.0 Vdc, I_C = 1.0 Adc, f = 1.0 kHz)	f_{hfe}	10	–	kHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*Indicates Within JEDEC Registration. (2N3055)

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

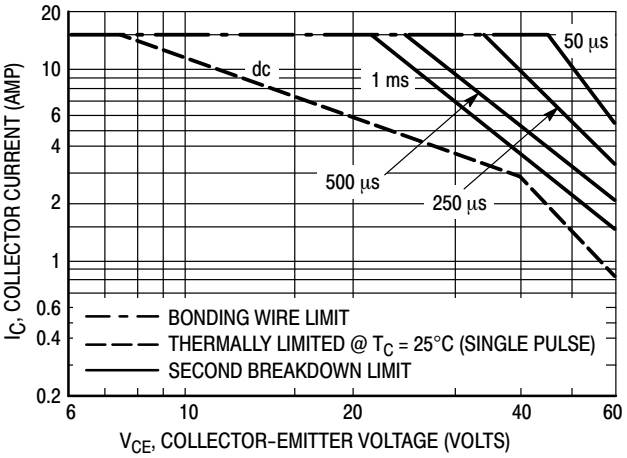


Figure 2. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on T_C = 25°C; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

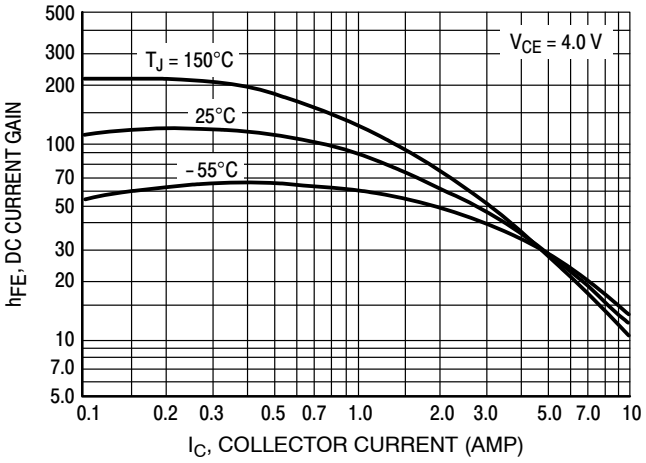


Figure 3. DC Current Gain, 2N3055 (NPN)

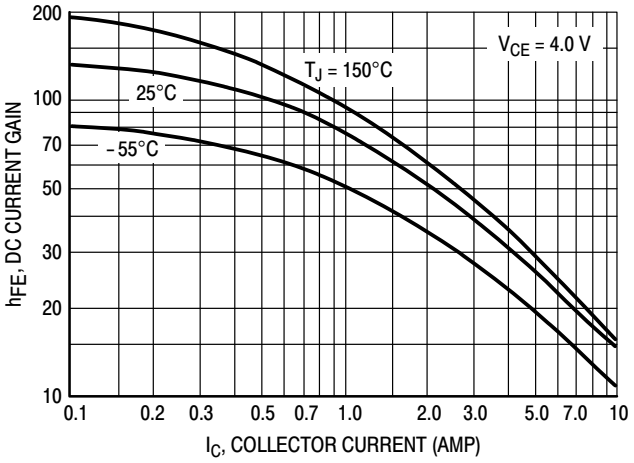


Figure 4. DC Current Gain, MJ2955 (PNP)

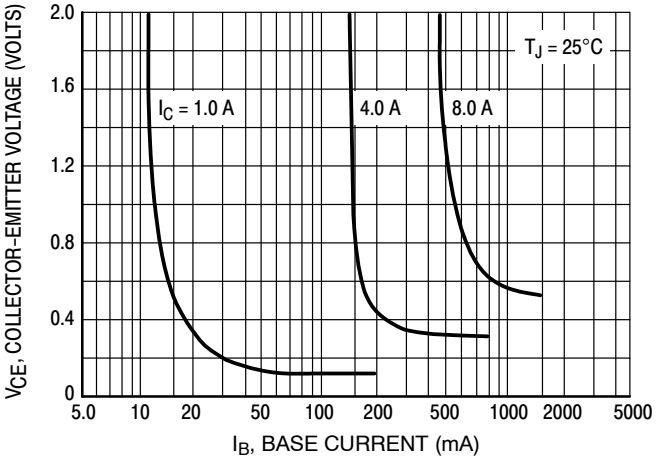


Figure 5. Collector Saturation Region, 2N3055 (NPN)

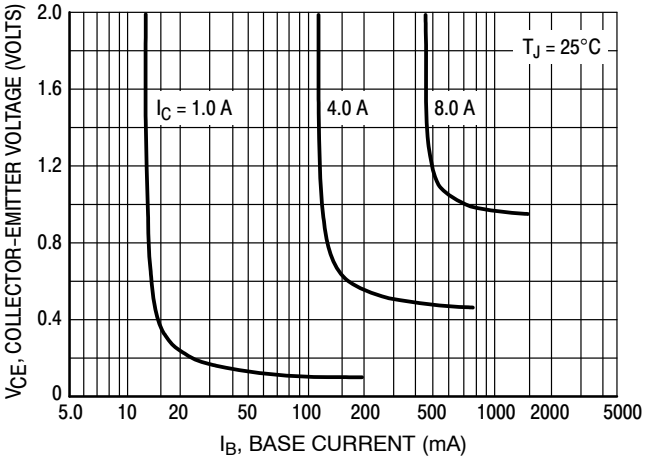


Figure 6. Collector Saturation Region, MJ2955 (PNP)

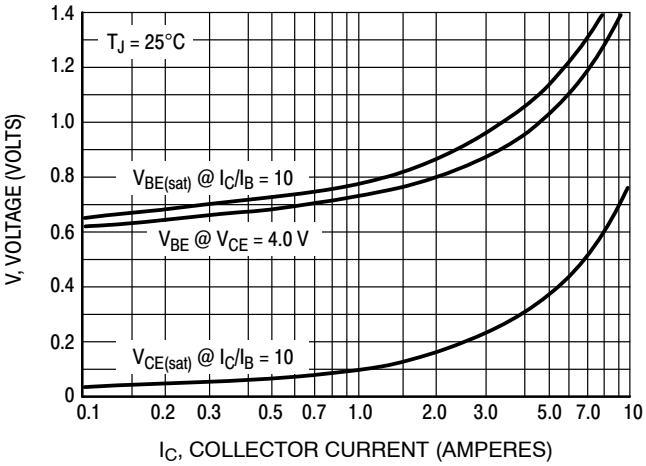


Figure 7. “On” Voltages, 2N3055 (NPN)

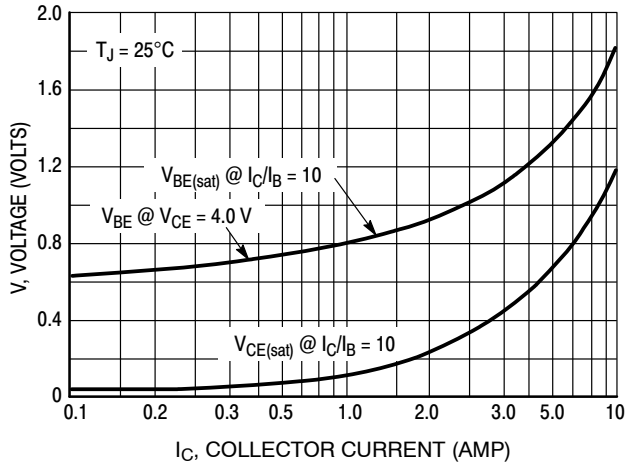
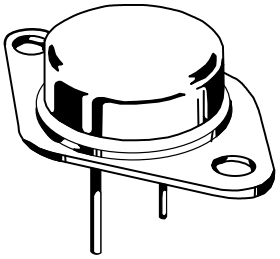


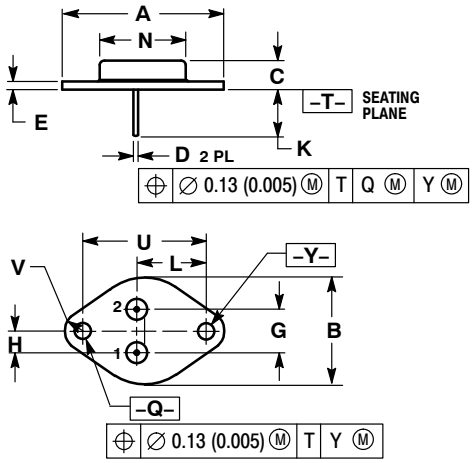
Figure 8. “On” Voltages, MJ2955 (PNP)



SCALE 1:1

TO−204 (TO−3)
CASE 1−07
ISSUE Z

DATE 10 MAR 2000



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO−204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

STYLE 2:
PIN 1. BASE
2. COLLECTOR
CASE: EMITTER

STYLE 3:
PIN 1. GATE
2. SOURCE
CASE: DRAIN

STYLE 4:
PIN 1. GROUND
2. INPUT
CASE: OUTPUT

STYLE 5:
PIN 1. CATHODE
2. EXTERNAL TRIP/DELAY
CASE: ANODE

STYLE 6:
PIN 1. GATE
2. EMITTER
CASE: COLLECTOR

STYLE 7:
PIN 1. ANODE
2. OPEN
CASE: CATHODE

STYLE 8:
PIN 1. CATHODE #1
2. CATHODE #2
CASE: ANODE

STYLE 9:
PIN 1. ANODE #1
2. ANODE #2
CASE: CATHODE

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
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